

Title (en)  
THERMAL ANALYSIS OF SEMICONDUCTOR DEVICES

Title (de)  
WÄRMEANALYSE VON HALBLEITERBAUELEMENTEN

Title (fr)  
ANALYSE THERMIQUE DE DISPOSITIFS SEMICONDUCTEURS

Publication  
**EP 3594669 B1 20210825 (EN)**

Application  
**EP 18183450 A 20180713**

Priority  
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Abstract (en)  
[origin: EP3594669A1] A method for determining a thermal impedance of a sample device is described. According to the method, a sample device is heated to an initial temperature. A pulsed power including a sequence of pulses is applied to the sample device. Temperature of the sample device is measured in a time-dependent manner. A thermal impedance of the sample device is determined based on the temperature of the sample device and the pulsed power.

IPC 8 full level  
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**EP 3594669 A1 20200115; EP 3594669 B1 20210825**; US 11313819 B2 20220426; US 2020018711 A1 20200116

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